
NIEC Announces Agreement with Cree for SiC Diodes in Japan

Hadano, Japan — July 18, 2007 — NIEC (Nihon Inter Electronics Corp.) (TSE:6974), a market leader in silicon-based discrete power semiconductors, today announced that it has signed an agreement under which NIEC will introduce next-generation silicon carbide (SiC)-based Schottky power rectifier diodes in Japan with die manufactured by Cree, Inc.

“Silicon carbide offers numerous concrete benefits over silicon-based rectifiers. Our market is showing growing demand for the far greater efficiency and performance offered by silicon carbide-based diodes, which enables reduced energy consumption in applications for home appliances including air conditioner and automotive invertors,” said Masao Ishii, president of NIEC. “Cree is the world’s leader in silicon carbide components and materials, and it only makes sense that we chose the leading products.”

“NIEC is a world leader in silicon-based Schottky rectifier diodes, and Cree is a world leader in silicon carbide-based rectifiers,” said John Palmour, Cree executive vice president for advanced devices. “We are excited about the potential impact the two companies can make on the Japanese market by combining our strengths.”

Compared with traditional silicon-based diodes, Cree’s SiC-based rectifiers can:

- Simplify power factor correction (PFC) boost design by eliminating the need for snubbers and reducing component count.

- Reduce power losses, leading to cooler operating temperatures.

- Produce significantly less electromagnetic interference (EMI)

Additional information about NIEC’s SiC-based Schottky power rectifier diodes may be obtained by calling NIEC at +81 33343 3411 or by visiting NIEC at www.niec.co.jp/english/.

About Nihon Inter Electronics Corporation

NIEC was founded in 1957 and was the first company to manufacture power silicon rectifier diodes in Japan. NIEC is a global leader in power management. The company manufactures high quality power semiconductor products which include silicon-based Schottky diodes, FREDs and standard rectifiers, conventional thyristors, power modules IGBTs and MOSFET, hybrid ICs and stack assembly for virtually every application. The company recently announced its first 200mm silicon wafer fab, now in full operation in Japan, as well as an existing 125mm silicon wafer fab. NIEC is a certified to TS/ISO16949 for special worldwide automotive requirements, ISO9001:2000 and ISO14001.

About Cree, Inc.

Cree is a market-leading innovator and manufacturer of semiconductors and devices that enhance the value of solid-state lighting, power and communications products by significantly increasing their en-



Nihon Inter Electronics Corporation

<http://www.niec.co.jp/>

ergy performance and efficiency.

Key to Cree's market advantage is its world-class materials expertise in SiC and gallium nitride (GaN) for chips and packaged devices that can handle more power in a smaller space while producing less heat than other available technologies, materials and products. Cree drives its increased performance technology into multiple applications including exciting alternatives in brighter and more tunable light for general illumination, backlighting for more vivid displays, optimized power management for high-current switch-mode power supplies and variable speed motors, and more effective wireless infrastructure for data and voice communications.

Cree customers range from innovative lighting fixtures makers to defense-related federal agencies. Cree's product families include blue and green LED chips, lighting LEDs, LED backlighting solutions, power-switching devices and radio-frequency/wireless devices. For product specifications please refer to www.cree.com.



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